Table A9.3 Intermediate load center systems

Project	Operational	Array	Inverter	Buyback
Mead, Nebraska	Jul '77	13.5 kW_{pk} Solarex 1.46 kW_{pk} Sensortech	NOVA 3 @ 10 kVa	None
Bryan, Ohio	Aug '79	15 kW_{pk} Solarex	DC	None
Mt. Laguna, California	Aug '79	49.5 kW_{pk} Solar Power 15.1 kW_{pk} Solarex	DECC 75 kVA	None
Natural Bridges National Monument, Utah	Jan '80	47.3 kW_{pk} Motorola 17.9 kW_{pk} Spectrolab 31.3 kW_{pk} ARCO	Cyberex 40 kVA	None
Newman Station, El Paso, Texas	Dec '80	17.5 kW_{pk} Solar Power	DC	None
Mississippi Country Community College, Blytheville, Arkansas	May '81	240 kW_{pk} Solar Kinetics Parabolic Trough-Solarex Cells	DECC 300 kVA	100%
Northwest Mississippi Junior College, Senatobia, Mississippi	Aug '81	50 kW_{pk} UTL GaAs 50 kW_{pk} Team 6X 50 kW_{pk} SKI-Solarex 1 kW_{pk} Photon Power CdS	Windworks 300 kVA	None
Lovington, New Mexico	Apr '81	100 kW_{pk} Solar Power	DECC 2 @ 60 kVA	None

(Continued)

Table A9.3 *(continued)*

Project	Operational	Array	Inverter	Buyback
Beverly HS, Beverly, Massachusetts	May '81	100 kW$_{pk}$ Solar Power	DECC 2 @ 60 kVA	100%
Oklahoma Museum of Science & Art, Oklahoma City, Oklahoma	Aug '81	135 kW$_{pk}$ Solarex (reflector)	Windworks 150 kVA	100%
BDM Office Building, Albuquerque, New Mexico	June '81	47 kW$_{pk}$ SKI Parabolic Trough—ASEC Cells	Westinghouse 62.5 kVA	None
Wilcox Hospital, Lihue, Kauai, Hawaii	Aug '81	35 kW$_{pk}$ Acurex Parabolic Trough—ASEC Cells	Westinghouse 62.5 kVA	None
Dallas-Fort Worth Airport	Nov '81	27 kW$_{pk}$ E-Systems Linear Fresnel—ASEC Cells	Jim Ross & Assoc. 27 kVA	None
Sea World, Orlando, Florida	Dec '81	110 kW$_{pk}$ GE Parabolic Trough	Windworks 150 kVA	None
Sky Harbor Airport, Phoenix, Arizona	Dec '81	225 kW$_{pk}$ Motorola PF Fresnel	Power Systems & Controls 250 kVA	None
San Bernardino West Side Community Dev. Corp. Concrete Plant, San Bernardino, California	Oct '81	35 kW$_{pk}$ Solarex	DECC 75 kVA	100%

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